ABSTRACT

**MEMORY ARRAY**

A memory array has a multiplicity of row conductors and a multiplicity of column conductors, the row conductors and column conductors being arranged to cross at cross-points, and has a memory cell disposed at each cross-point, each memory cell having a storage element and a control element coupled in series between a row conductor and a column conductor, and each control element including a silicon-rich insulator. Methods for fabricating the memory array are disclosed.